



AFRL-RY-WP-TP-2010-1243

**5-W YELLOW LASER BY INTRACAVITY FREQUENCY
DOUBLING OF HIGH-POWER VERTICAL-EXTERNAL-
CAVITY SURFACE-EMITTING LASER (POSTPRINT)**

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OCTOBER 2008

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UNITED STATES AIR FORCE**

REPORT DOCUMENTATION PAGE					<i>Form Approved</i> OMB No. 0704-0188	
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1. REPORT DATE (DD-MM-YY) October 2008		2. REPORT TYPE Journal Article Postprint		3. DATES COVERED (From - To) 01 January 2008 – 01 September 2008		
4. TITLE AND SUBTITLE 5-W YELLOW LASER BY INTRACAVITY FREQUENCY DOUBLING OF HIGH-POWER VERTICAL-EXTERNAL-CAVITY SURFACE-EMITTING LASER (POSTPRINT)				5a. CONTRACT NUMBER In-house		
				5b. GRANT NUMBER		
				5c. PROGRAM ELEMENT NUMBER 62204F		
6. AUTHOR(S) Mahmoud Fallahi, Li Fan, Chris Hessenius, Jörg Hader, Hongbo Li, and Jerome V. Moloney (University of Arizona) Bernardette Kunert, Wolfgang Stolz, and Stephan W. Koch (Philipps Universität Marburg) James T. Murray (Areté Associates) Robert Bedford (AFRL/RYPD)				5d. PROJECT NUMBER 2002		
				5e. TASK NUMBER IH		
				5f. WORK UNIT NUMBER 2002IH0E		
7. PERFORMING ORGANIZATION NAME(S) AND ADDRESS(ES) University of Arizona Arizona Center for Mathematical Sciences Tucson, AZ 85721 ----- Philipps Universität Marburg Department of Physics and Material Sciences Center Renthof 5, 35032 Marburg, Germany ----- Arété Associates 1225 Ken Pratt Boulevard Longmont, CO 80501				8. PERFORMING ORGANIZATION REPORT NUMBER AFRL-RY-WP-TP-2010-1243		
9. SPONSORING/MONITORING AGENCY NAME(S) AND ADDRESS(ES) Air Force Research Laboratory Sensors Directorate Wright-Patterson Air Force Base, OH 45433-7320 Air Force Materiel Command United States Air Force				10. SPONSORING/MONITORING AGENCY ACRONYM(S) AFRL/RYPD		
				11. SPONSORING/MONITORING AGENCY REPORT NUMBER(S) AFRL-RY-WP-TP-2010-1243		
12. DISTRIBUTION/AVAILABILITY STATEMENT Approved for public release; distribution unlimited.						
13. SUPPLEMENTARY NOTES Journal article published in <i>IEEE Photonics Technology Letters</i> , Vol. 20, No. 20, October 15, 2008. PAO Case Number: 88ABW-08-3883; Clearance Date: 26 Jun 2008. Paper contains color. © 2008 IEEE. The U.S. Government is joint author of the work and has the right to use, modify, reproduce, release, perform, display, or disclose the work.						
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15. SUBJECT TERMS lasers, semiconductor						
16. SECURITY CLASSIFICATION OF:			17. LIMITATION OF ABSTRACT: SAR	18. NUMBER OF PAGES 10	19a. NAME OF RESPONSIBLE PERSON (Monitor) Robert Bedford 19b. TELEPHONE NUMBER (Include Area Code) N/A	
a. REPORT Unclassified	b. ABSTRACT Unclassified	c. THIS PAGE Unclassified				

5-W Yellow Laser by Intracavity Frequency Doubling of High-Power Vertical-External-Cavity Surface-Emitting Laser

Mahmoud Fallahi, Li Fan, Yushi Kaneda, Chris Hessenius, Jörg Hader, Hongbo Li, Jerome V. Moloney, Bernardette Kunert, Wolfgang Stolz, Stephan W. Koch, James Murray, and Robert Bedford

Abstract—We report on the development of a high-power tunable yellow–orange laser. It is based on intracavity frequency doubling of a widely tunable, highly strained InGaAs–GaAs vertical-external-cavity surface-emitting laser operating near 1175 nm. Over 5 W of continuous-wave output power is achieved and is tunable over a 15-nm band centered at 587 nm. This compact low-cost high-power yellow–orange laser provides an innovative alternative for sodium guidestar lasers, medical and communication applications.

Index Terms—Intracavity frequency doubling, optically pumped semiconductor lasers, tunable vertical-external-cavity surface-emitting laser (VECSEL).

I. INTRODUCTION

HIGH-POWER laser sources covering the 570- to 590-nm bands are of great interest for a wide range of applications including sodium guidestar laser, quantum computing, and medical applications [1], [2]. Despite the wide range of applications, the development of yellow–orange lasers has been limited, primarily due to a lack of gain materials within this band. Nonlinear frequency conversion has frequently been used to generate emission in the yellow–orange range. Several methods including frequency doubling of Yb solid-state lasers [3], frequency doubling of Raman-shifted Yb (Nd) lasers [4], and frequency doubling of Bi-doped fiber lasers [5] have been investigated. Unfortunately a majority of these approaches suffer from limited emission range, low output power, and high cost. Development of a semiconductor-based yellow laser is very attractive

for their high-gain, large volume production, and low cost. Strained multiquantum-well semiconductor lasers are widely used in the near infrared range. However, due to their limited direct bandgap energy, a range of visible emission wavelengths are difficult to fabricate.

Optically pumped vertical-external-cavity surface-emitting lasers (VECSELs) using multiquantum wells are very attractive as low-cost high-power high-brightness sources [6], [7]. In addition, by having access to the intracavity, several attractive features such as wavelength tuning, frequency doubling for visible generation, and Q -switching can be achieved.

Here we report on the development and demonstration of a highly strained InGaAs–GaAs VECSEL which can cover a significantly longer wavelength range of 1147–1197 nm. Very robust multi-Watt high-brightness performance at room temperature is demonstrated. Using intracavity frequency doubling we demonstrate high-power coherent emission in a wide yellow–orange band (575–595 nm).

II. DESIGN AND FABRICATION

Strained InGaAs–GaAs quantum-well (QW) lasers are widely used for the generation of 900- to 1100-nm lasers. However longer wavelengths are a major challenge and require careful design and growth of the structure. The design of the 1180-nm VECSEL structure is accomplished using rigorous many-body microscopic quantum design tools and 3-D optical/thermal modeling of the device [7]. This microscopic quantum design approach utilizes a closed-loop semiconductor laser design tool that is free of adjustable fit parameters, and rigorously computes the low-intensity photoluminescence (PL) spectra, semiconductor gain (and refractive index) spectra, and spontaneous and Auger recombination losses for the specific QW structure. Computed low-intensity PL spectra are used for wafer diagnostics and quality control. The quantum design is then coupled with 3-D optical/thermal modeling of the device. A highly strain compensated InGaAs–GaAs–GaAsP multiquantum well in a resonant periodic gain (RPG) structure was designed using the modeling tool.

The designed InGaAs–GaAs VECSEL structure was grown using a low-temperature metal–organic vapor phase epitaxial (MOVPE) process. MOVPE growth uses alternative group-V liquid sources [tertiarybutylarsine (TBA); tertiarybutylphosphine (TBP)] that decompose at lower temperatures than the conventional hydride precursors [8]. This allows for a general

Manuscript received June 17, 2008; revised July 19, 2008. First published August 22, 2008; current version published September 26, 2008. This work was supported by the U.S. Air Force Office of Scientific Research under a Phase II STTR Grant (FA9550-06-C-0044). The work of M. Fallahi was supported by the National Science Foundation (NSF).

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Digital Object Identifier 10.1109/LPT.2008.2003413

reduction of the growth temperature, promoting higher values of strain and, thus, reproducibly higher indium-concentrations in the active QW. In addition, GaAsP barriers with precise chemical composition are grown to balance the QW strain. These factors enable growth of InGaAs epitaxial structure achieving lasing at the target wavelength of 1175 nm.

The VECSEL structure consists of ten repeats of compressive strained InGaAs QWs. Each QW is 7 nm thick and surrounded by GaAsP strain compensation layers and GaAs barriers, in which the 808-nm pump emission is absorbed. The thickness and compositions of the layers are optimized such that each QW is positioned at the antinodes of the cavity standing wave to provide RPG in the active region. A high reflectivity ($R > 99.5\%$) distributed Bragg reflector (DBR) stack made of 21 pairs of Al-GaAs-AlAs is grown on the top of the active region. To avoid premature thermal rollover, a detuning between QW gain peak and microcavity resonance of about 30 nm is introduced which compensates the thermal detuning at higher temperatures and powers at the expense of a slight increase in threshold power.

Extraction of the quantum defect heat from the active region presents another challenge in the development of high-power lasers. The large energy difference between the pump and lasing wavelength lowers the quantum efficiency of the laser and generates more waste heat in the active region. For efficient heat dissipation, after a thin Ti-Au metallization, the epitaxial side of the wafer is mounted on a chemical vapor deposition diamond heat spreader using indium solder. The GaAs substrate is then completely removed by selective wet chemical etching. The remaining semiconductor, consisting of a DBR stack and RPG active layers, is about 6 μm thick allowing efficient heat extraction at high pumping energy. The surface quality of the VECSEL sample is characterized by a WYKO NT-2000 interferometer, and a peak-to-valley height of less than 40 nm over an area of 0.5 mm \times 0.5 mm is measured. This optically smooth surface makes the scattering/diffraction loss negligible and results in high slope efficiency and high beam quality. Finally in order to reduce the surface reflectivity and subcavity resonance effect a dielectric antireflection (AR) coating is deposited. The processed VECSEL chip is mounted on a heat sink for temperature control.

III. EXPERIMENTAL RESULTS

To generate a coherent fundamental and yellow-orange laser, we used the folded cavity of Fig. 1, in which the VECSEL chip and a flat mirror serve as two end mirrors and a concave spherical mirror as the folding mirror. L1 and L2 are around 10 and 4.5 cm, respectively, with a full folding angle of about 30° . The folding concave mirror with a radius of curvature of 75 mm is high-reflective coated for the fundamental laser but is highly transmissive ($\sim 95\%$) at the yellow-orange wavelength. The laser is characterized by focusing an incoherent fiber-coupled 808-nm pump source on the chip with a spot size of 500 μm in diameter. First in order to characterize the performance of the fundamental (~ 1175 nm) VECSEL, a flat output mirror with a reflectivity of 96% is used. Fig. 2 shows the performance of the laser at 15 $^\circ\text{C}$ and 25 $^\circ\text{C}$ heat-sink temperatures for a 500- μm

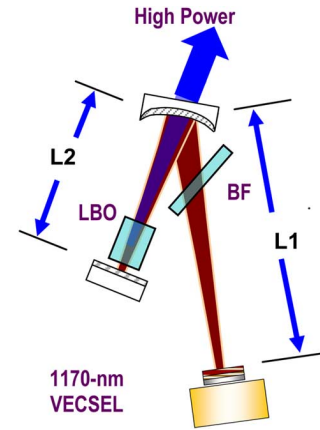


Fig. 1. Schematic of the VECSEL cavity setup for yellow-orange generation.

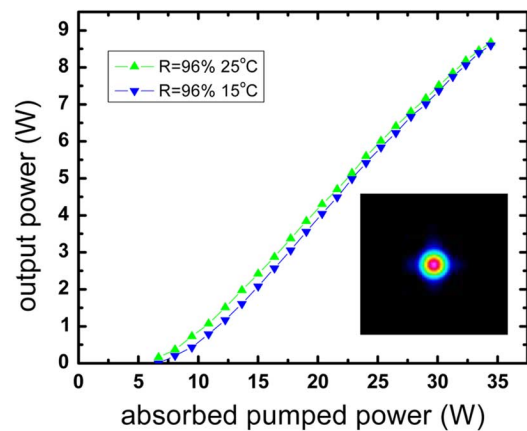


Fig. 2. VECSEL fundamental output power versus net pump power and the beam quality at 7-W output ($M^2 < 1.5$).

pump spot. Maximum continuous-wave output power can reach 8.6 W at room temperature. The slope efficiency is around 35% at room temperature. The M^2 factor slowly increases from 1.03 at threshold to 1.5- at 8.6-W output, indicating a near TEM₀₀ transverse mode at high-power operation. At an output power of 8 W, the free lasing wavelengths are 1174 and 1175 nm at 15 $^\circ\text{C}$ and 25 $^\circ\text{C}$, respectively. Linewidth narrowing and wavelength tuning is achieved by using an intracavity birefringent filter (BF), which is inserted at Brewster's angle. By using this low-loss filter, we can achieve over 30-nm wavelength tuning. The output power variation is less than 10% in the tuning range of 1170–1180 nm, making the laser suitable for yellow-orange operation.

For efficient intracavity frequency doubling, we increased the cavity Q by replacing the 96% flat outcoupler with a highly reflecting mirror. In such a cavity the fundamental wavelength can be further tuned in the 1150- to 1195-nm wavelength range. A lithium triborate (LBO) crystal with a size of 3 mm \times 3 mm \times 10 mm normally cut for the 1178- to 589-nm conversion is then inserted close to the flat mirror, providing a Type-I angular phase-matching condition (Fig. 1). Both facets of the LBO are AR coated for both the fundamental laser (1178 nm) and SHG signal (589 nm). Fig. 3 shows the total yellow output for a 500- μm pump spot size. At this pump spot, over 5 W at 585

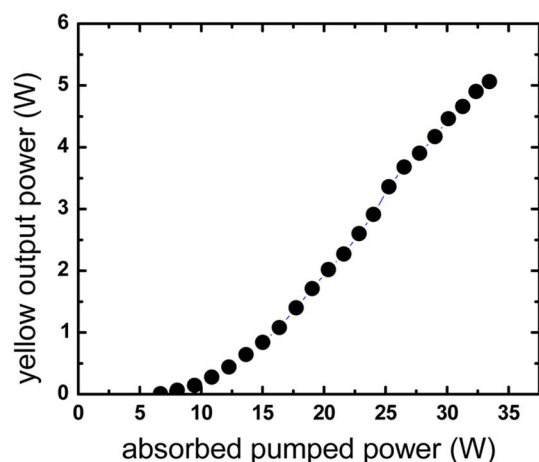


Fig. 3. Yellow laser output power versus the absorbed pump power.

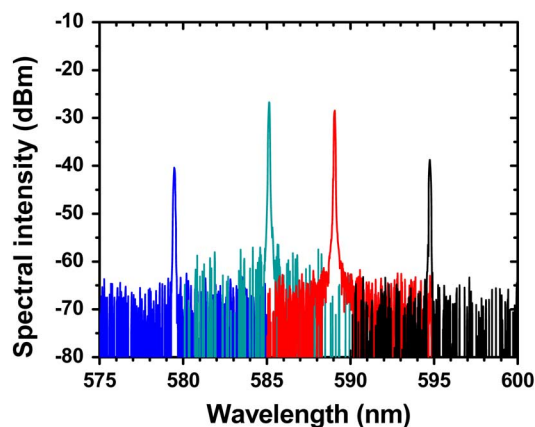


Fig. 4. Yellow-orange wavelength tuning spectra.

and 589 nm is generated. The overall pump optical power to yellow optical conversion efficiency exceeds 14% at 589-nm SHG, which is the result of high-performance fundamental generation and the efficiency of intracavity frequency doubling. A wide tuning range covering 580 to 595 nm is also achieved (Fig. 4). In the tuning range, we lock the fundamental wavelength at 1159, 1170, 1178, and 1190 nm, respectively, and align

the phase matching angle of the LBO crystal to optimize the yellow-orange output. The yellow laser linewidth is around four angstroms, and can be further reduced to subangstrom by incorporating an intracavity Fabry-Pérot etalon in conjunction with the BF.

IV. CONCLUSION

We have demonstrated an efficient yellow laser by intracavity frequency doubling of a highly strained InGaAs-GaAs tunable VECSEL laser with an output power in excess of 8 W at around 1175 nm. Full wavelength tuning in the 1150- to 1190-nm range has been demonstrated using a folded high- Q cavity. High-power broadband output in the yellow-orange band (579- to 595-nm bands) is achieved through intracavity frequency doubling. Over 5-W yellow-orange tunable output power has been demonstrated over the 585- to 589-nm bands. This laser promises to be a reliable alternative for high-power, compact, and low-cost yellow lasers.

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